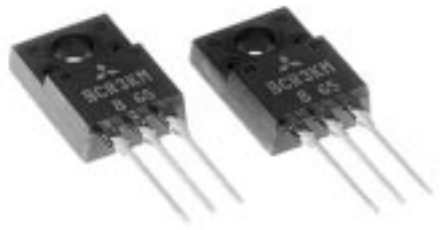
BCR3KM

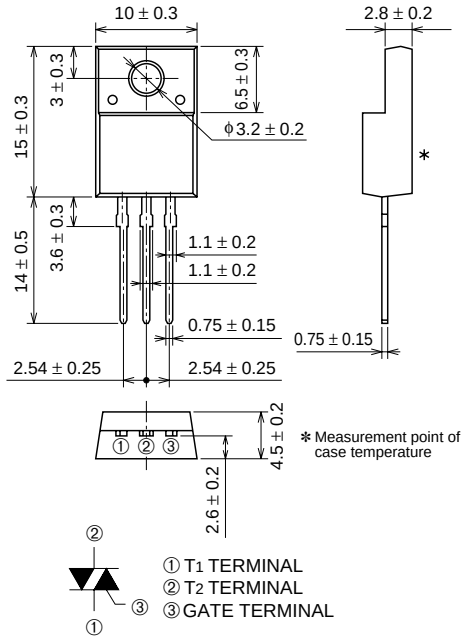
LOW POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

BCR3KM



- $I_{T\ (RMS)}$ ····· 3A
- V_{DRM} ····· 400V / 600V
- $I_{FGT\ I}$, $I_{RGT\ I}$, $I_{RGT\ III}$ ····· 15mA (10mA) ✻2
- UL Recognized : File No. E80271

OUTLINE DRAWING Dimensions in mm



TO-220FN

APPLICATION

Control of heater such as electric rice cooker, electric pot

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8	12	
V_{DRM}	Repetitive peak off-state voltage✻1	400	600	V
V_{DSM}	Non-repetitive peak off-state voltage✻1	500	720	V

Symbol	Parameter	Conditions	Ratings	Unit
$I_{T\ (RMS)}$	RMS on-state current	Commercial frequency, sine full wave 360° conduction, Tc=111°C	3	A
I_{TSM}	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	30	A
I^2t	I^2t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	3.7	A^2s
P_{GM}	Peak gate power dissipation		3	W
$P_{G\ (AV)}$	Average gate power dissipation		0.3	W
V_{GM}	Peak gate voltage		6	V
I_{GM}	Peak gate current		0.5	A
T_j	Junction temperature		–40 ~ +125	°C
T_{stg}	Storage temperature		–40 ~ +125	°C
—	Weight		2.0	g
V_{iso}	Isolation voltage	T_a=25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case	2000	V

✻1. Gate open.

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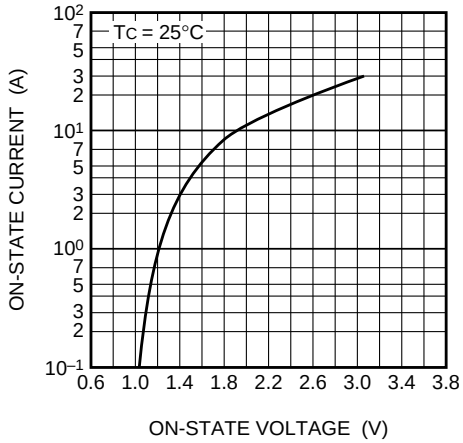
ELECTRICAL CHARACTERISTICS

Symbol	Parameter		Test conditions	Limits			Unit
				Min.	Typ.	Max.	
I_{DRM}	Repetitive peak off-state current		T_j=125°C, V_{DRM} applied	—	—	2.0	mA
V_{TM}	On-state voltage		T_c=25°C, I_{TM}=4.5A, Instantaneous measurement	—	—	1.5	V
$V_{FGT\ I}$	Gate trigger voltage *2	I	T_j=25°C, V_D=6V, R_L=6Ω, R_G=330Ω	—	—	1.5	V
$V_{RGT\ I}$		II		—	—	1.5	V
$V_{RGT\ III}$		III		—	—	1.5	V
$I_{FGT\ I}$	Gate trigger current *2	I	T_j=25°C, V_D=6V, R_L=6Ω, R_G=330Ω	—	—	15*2	mA
$I_{RGT\ I}$		II		—	—	15*2	mA
$I_{RGT\ III}$		III		—	—	15*2	mA
V_{GD}	Gate non-trigger voltage		T_j=125°C, V_D=1/2V_{DRM}	0.2	—	—	V
$R_{th\ (j-c)}$	Thermal resistance		Junction to case *3	—	—	4.0	°C/W
$R_{th\ (j-a)}$	Thermal resistance		Junction to ambient	—	—	50	°C/W

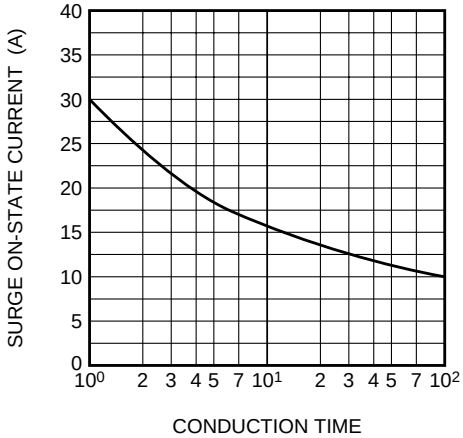
*2. High sensitivity (I_{GT}≤ 10mA) is also available. (I_{GT} item ①)
*3. The contact thermal resistance $R_{th\ (c-f)}$ in case of greasing is 0.5°C/W.

PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTICS



RATED SURGE ON-STATE CURRENT



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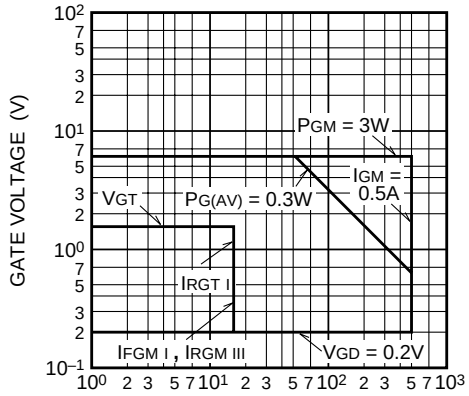
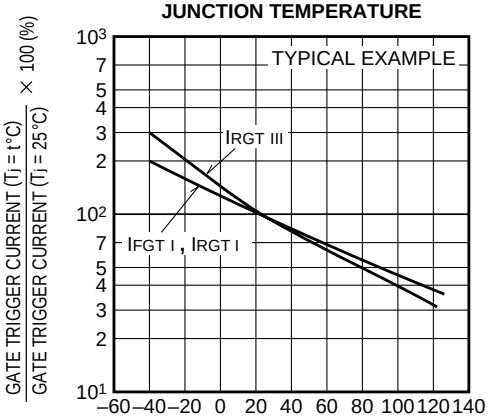
LOW POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

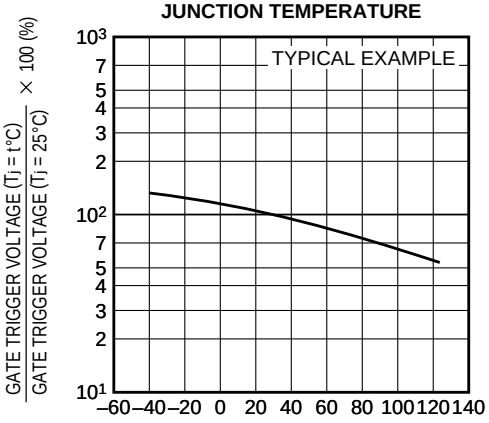
GATE CHARACTERISTICS (I, II AND III)



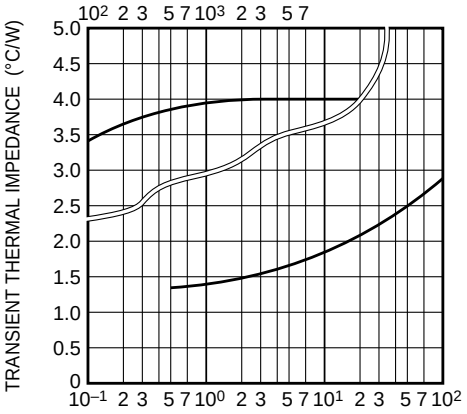
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



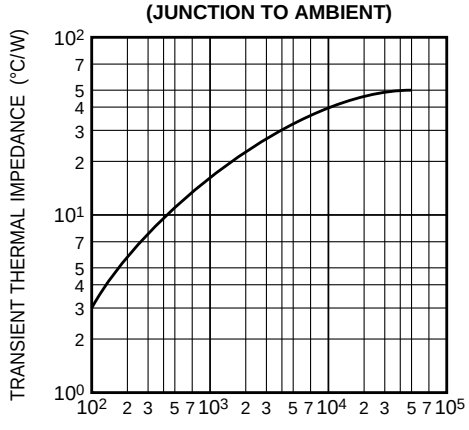
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



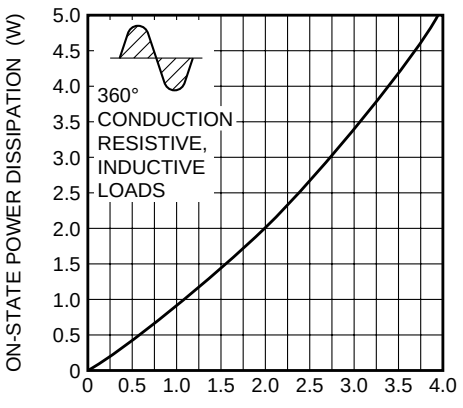
MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)



MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO AMBIENT)



MAXIMUM ON-STATE POWER DISSIPATION



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LOW POWER USE
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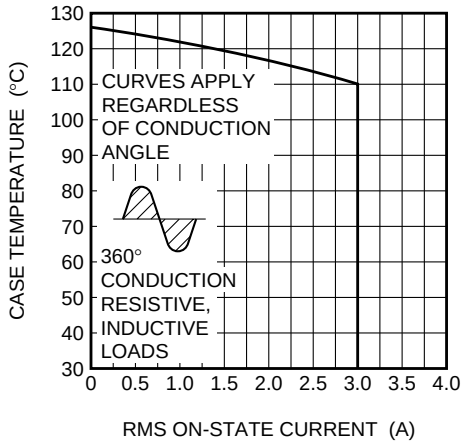
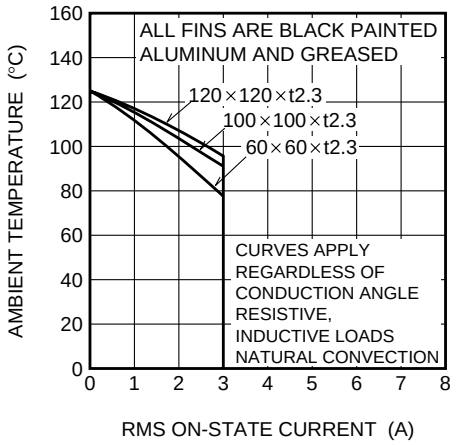
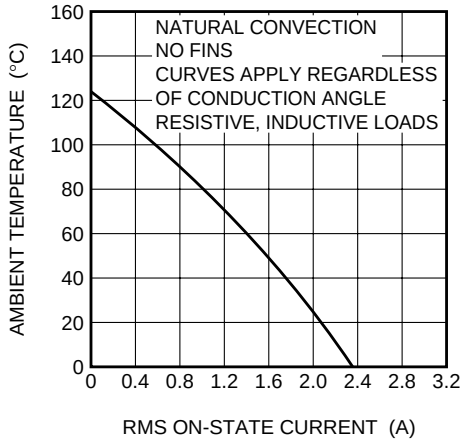
ALLOWABLE CASE TEMPERATURE VS. RMS ON-STATE CURRENT



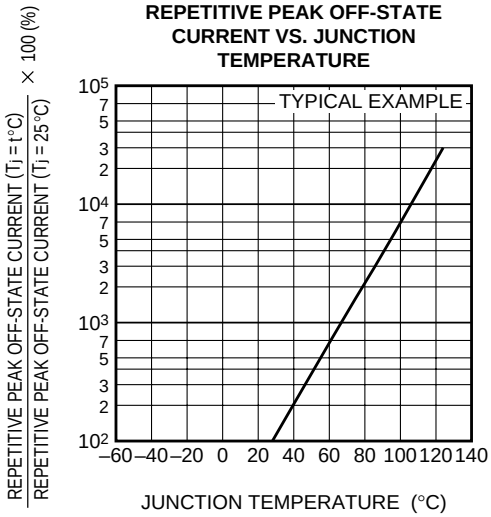
ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT



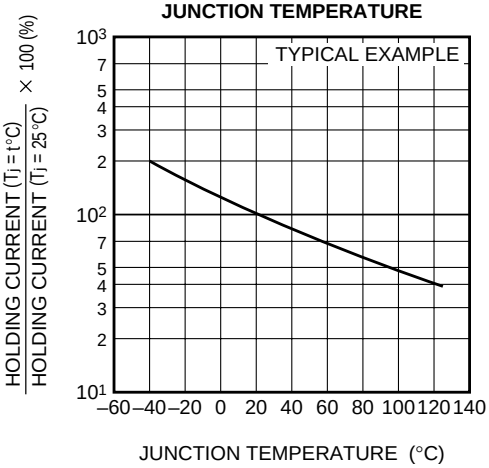
ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT



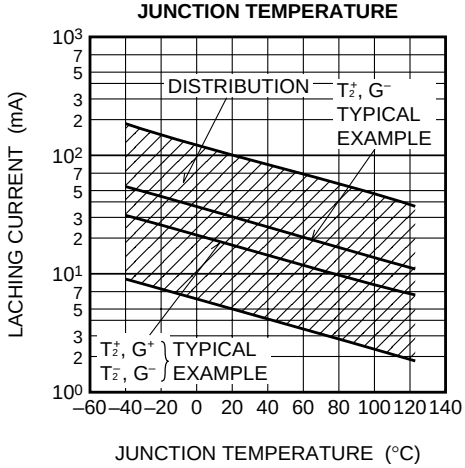
REPETITIVE PEAK OFF-STATE CURRENT VS. JUNCTION TEMPERATURE



HOLDING CURRENT VS. JUNCTION TEMPERATURE



LACHING CURRENT VS. JUNCTION TEMPERATURE



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LOW POWER USE
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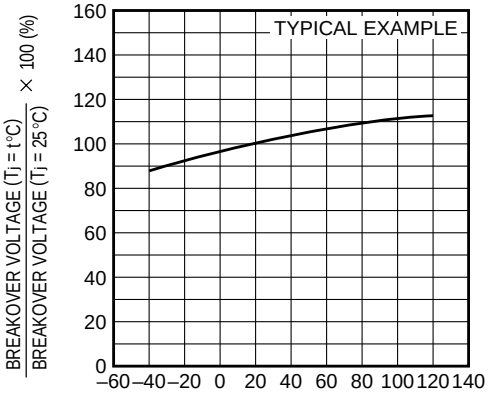
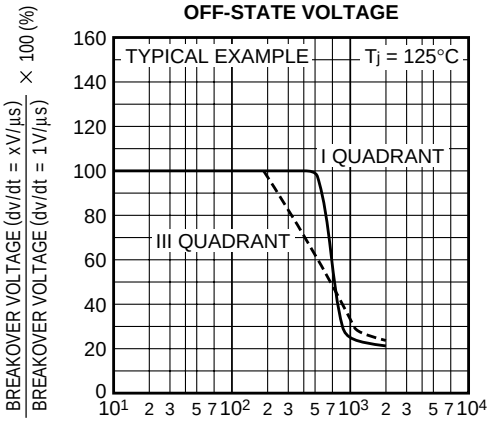
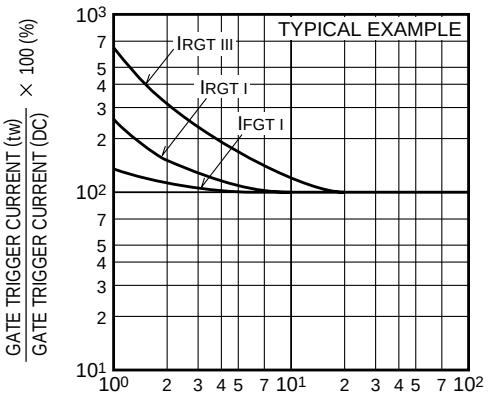
BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE



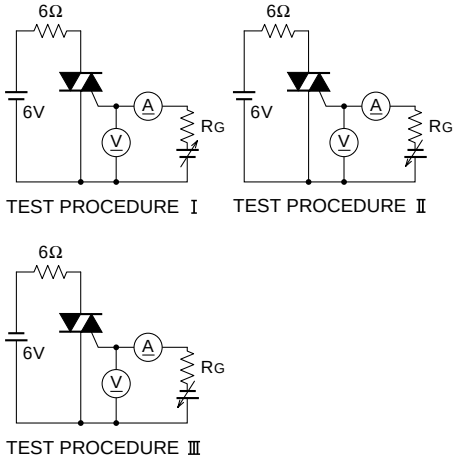
BREAKOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE



GATE TRIGGER CURRENT VS. GATE CURRENT PULSE WIDTH



GATE TRIGGER CHARACTERISTICS TEST CIRCUITS



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